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### Applications of "[Embedded - Microcontrollers](#)"

#### Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I <sup>2</sup> C, LINbus, SPI, UART, USB
Peripherals	DMA, I <sup>2</sup> S, LED, POR, PWM, WDT
Number of I/O	55
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	160K x 8
Voltage - Supply (Vcc/Vdd)	3.13V ~ 3.63V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-100-11
Purchase URL	<a href="https://www.e-xfl.com/product-detail/infineon-technologies/xmc4500f100k1024acxqsa1">https://www.e-xfl.com/product-detail/infineon-technologies/xmc4500f100k1024acxqsa1</a>

## XMC4500 Data Sheet

### Revision History: V1.4 2016-01

#### Previous Versions:

V1.3, 2014-03

V1.2, 2013-07

V1.1, 2013-07

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V0.8, 2012-11

Page	Subjects
<b>43</b>	Added information that <u>PORST</u> Pull-up is identical to the pull-up on standard I/O pins.
<b>42</b>	Added footnote explaining minimum $V_{BAT}$ requirements to start the hibernate domain and/or oscillation of a crystal on RTC_XTAL.
<b>59</b>	Corrected parameter name of of USB pull device (upstream port receiving) definition according to USB standard (referenced to DM instead of DP)
<b>61</b>	Relaxed RTC_XTAL $V_{PPX}$ parameter value and changed it to a system requirement.
<b>115ff</b>	Added PG-LQFP-100-25 and PG-LQFP-144-24 package information.
<b>115</b>	Added tables describing the differences between PG-LQFP-100-11 to PG-LQFP-100-25 as well as PG-LQFP-144-18 to PG-LQFP-144-24 packages.

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**Table of Contents**

3.3.6	JTAG Interface Timing . . . . .	76
3.3.7	Serial Wire Debug Port (SW-DP) Timing . . . . .	78
3.3.8	Embedded Trace Macro Cell (ETM) Timing . . . . .	79
3.3.9	Peripheral Timing . . . . .	80
3.3.9.1	Delta-Sigma Demodulator Digital Interface Timing . . . . .	80
3.3.9.2	Synchronous Serial Interface (USIC SSC) Timing . . . . .	81
3.3.9.3	Inter-IC (IIC) Interface Timing . . . . .	84
3.3.9.4	Inter-IC Sound (IIS) Interface Timing . . . . .	86
3.3.9.5	SDMMC Interface Timing . . . . .	88
3.3.10	EBU Timing . . . . .	96
3.3.10.1	EBU Asynchronous Timing . . . . .	96
3.3.10.2	EBU Burst Mode Access Timing . . . . .	103
3.3.10.3	EBU Arbitration Signal Timing . . . . .	105
3.3.10.4	EBU SDRAM Access Timing . . . . .	106
3.3.11	USB Interface Characteristics . . . . .	110
3.3.12	Ethernet Interface (ETH) Characteristics . . . . .	111
3.3.12.1	ETH Measurement Reference Points . . . . .	111
3.3.12.2	ETH Management Signal Parameters (ETH_MDC, ETH_MDIO) . .	112
3.3.12.3	ETH MII Parameters . . . . .	113
3.3.12.4	ETH RMII Parameters . . . . .	114
<b>4</b>	<b>Package and Reliability . . . . .</b>	<b>115</b>
4.1	Package Parameters . . . . .	115
4.1.1	Thermal Considerations . . . . .	115
4.2	Package Outlines . . . . .	117
4.3	Quality Declarations . . . . .	122

## **About this Document**

This Data Sheet is addressed to embedded hardware and software developers. It provides the reader with detailed descriptions about the ordering designations, available features, electrical and physical characteristics of the XMC4500 series devices.

The document describes the characteristics of a superset of the XMC4500 series devices. For simplicity, the various device types are referred to by the collective term XMC4500 throughout this manual.

### **XMC4000 Family User Documentation**

The set of user documentation includes:

- **Reference Manual**
  - describes the functionality of the superset of devices.
- **Data Sheets**
  - list the complete ordering designations, available features and electrical characteristics of derivative devices.
- **Errata Sheets**
  - list deviations from the specifications given in the related Reference Manual or Data Sheets. Errata Sheets are provided for the superset of devices.

***Attention: Please consult all parts of the documentation set to attain consolidated knowledge about your device.***

Application related guidance is provided by **Users Guides** and **Application Notes**.

Please refer to <http://www.infineon.com/xmc4000> to get access to the latest versions of those documents.

**Summary of Features**

**Table 2 Features of XMC4500 Device Types (cont'd)**

Derivative <sup>1)</sup>	LEDTS Intf.	SDMMC Intf.	EBU Intf. <sup>2)</sup>	ETH Intf. <sup>3)</sup>	USB Intf.	USIC Chan.	MultiCAN Nodes, MO
XMC4504-F144x512	1	1	SDM	-	-	3 x 2	-
XMC4504-F100x512	1	1	M16	-	-	3 x 2	-

1) x is a placeholder for the supported temperature range.

2) Memory types supported S=SDRAM, D=DEMUX, M=MUX 16-bit and 32-bit, M16=MUX 16-bit

3) Supported interfaces, M=MII, R=RMII.

**Table 3 Features of XMC4500 Device Types**

Derivative <sup>1)</sup>	ADC Chan.	DSD Chan.	DAC Chan.	CCU4 Slice	CCU8 Slice	POSIF Intf.
XMC4500-E144x1024	32	4	2	4 x 4	2 x 4	2
XMC4500-F144x1024	32	4	2	4 x 4	2 x 4	2
XMC4500-F100x1024	24	4	2	4 x 4	2 x 4	2
XMC4500-F144x768	32	4	2	4 x 4	2 x 4	2
XMC4500-F100x768	24	4	2	4 x 4	2 x 4	2
XMC4502-F100x768	24	4	2	4 x 4	2 x 4	2
XMC4504-F144x512	32	4	2	4 x 4	2 x 4	2
XMC4504-F100x512	24	4	2	4 x 4	2 x 4	2

1) x is a placeholder for the supported temperature range.

## 1.4 Definition of Feature Variants

The XMC4500 types are offered with several memory sizes and number of available VADC channels. [Table 4](#) describes the location of the available Flash memory, [Table 5](#) describes the location of the available SRAMs, [Table 6](#) the available VADC channels.

**Table 4 Flash Memory Ranges**

Total Flash Size	Cached Range	Uncached Range
512 Kbytes	0800 0000 <sub>H</sub> – 0807 FFFF <sub>H</sub>	0C00 0000 <sub>H</sub> – 0C07 FFFF <sub>H</sub>

**General Device Information**
**Table 9 Package Pin Mapping (cont'd)**

Function	LQFP-144	LFBGA-144	LQFP-100	Pad Type	Notes
P0.11	139	E5	95	A1+	
P0.12	138	D5	94	A1+	
P0.13	137	C5	-	A1+	
P0.14	136	E6	-	A1+	
P0.15	135	C6	-	A1+	
P1.0	112	D9	79	A1+	
P1.1	111	E9	78	A1+	
P1.2	110	C11	77	A2	
P1.3	109	C12	76	A2	
P1.4	108	C10	75	A1+	
P1.5	107	D10	74	A1+	
P1.6	116	B9	83	A2	
P1.7	115	B10	82	A2	
P1.8	114	A10	81	A2	
P1.9	113	B11	80	A2	
P1.10	106	D12	73	A1+	
P1.11	105	D11	72	A1+	
P1.12	104	E11	71	A2	
P1.13	103	E12	70	A2	
P1.14	102	E10	69	A2	
P1.15	94	G12	68	A2	
P2.0	74	J11	52	A2	
P2.1	73	K12	51	A2	After a system reset, via HWSEL this pin selects the DB.TDO function.
P2.2	72	K11	50	A2	
P2.3	71	L11	49	A2	
P2.4	70	L10	48	A2	
P2.5	69	M10	47	A2	
P2.6	76	J9	54	A1+	
P2.7	75	K9	53	A1+	
P2.8	68	L9	46	A2	
P2.9	67	M9	45	A2	

**General Device Information**

**Table 9 Package Pin Mapping (cont'd)**

Function	LQFP-144	LFBGA-144	LQFP-100	Pad Type	Notes
P2.10	66	L8	44	A2	
P2.11	65	M8	-	A2	
P2.12	64	L7	-	A2	
P2.13	63	M7	-	A2	
P2.14	60	K7	41	A2	
P2.15	59	J6	40	A2	
P3.0	7	C1	7	A2	
P3.1	6	B2	6	A2	
P3.2	5	B3	5	A2	
P3.3	132	F7	93	A1+	
P3.4	131	E7	92	A1+	
P3.5	130	B6	91	A2	
P3.6	129	A7	90	A2	
P3.7	14	E4	-	A1+	
P3.8	13	E3	-	A1+	
P3.9	12	F5	-	A1+	
P3.10	11	F6	-	A1+	
P3.11	10	D3	-	A1+	
P3.12	9	D2	-	A2	
P3.13	8	C2	-	A2	
P3.14	134	D6	-	A1+	
P3.15	133	D7	-	A1+	
P4.0	124	B8	85	A2	
P4.1	123	A9	84	A2	
P4.2	122	E8	-	A1+	
P4.3	121	F8	-	A1+	
P4.4	120	C7	-	A1+	
P4.5	119	D8	-	A1+	
P4.6	118	C8	-	A1+	
P4.7	117	C9	-	A1+	
P5.0	84	H9	58	A1+	
P5.1	83	H8	57	A1+	
P5.2	82	H7	56	A1+	

**General Device Information**

**Table 9 Package Pin Mapping (cont'd)**

Function	LQFP-144	LFBGA-144	LQFP-100	Pad Type	Notes
VSSO	89	J12	63	Power	
VSS	Exp. Pad	-	Exp. Pad	Power	<p><b>Exposed Die Pad</b> The exposed die pad is connected internally to VSS. For proper operation, it is mandatory to connect the exposed pad directly to the common ground on the board. For thermal aspects, please refer to the Data Sheet. Board layout examples are given in an application note.</p>

## 2.2.2.1 Port I/O Function Table

**Table 11 Port I/O Functions**

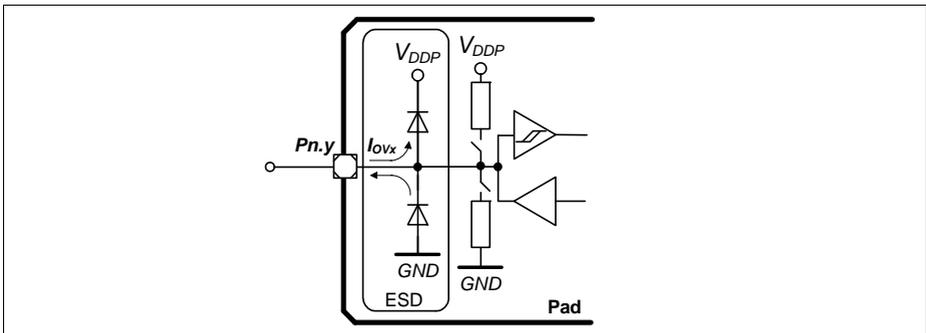
Function	Outputs						Inputs										
	ALT1	ALT2	ALT3	ALT4	HWO0	HWO1	HWI0	HWI1	Input	Input	Input	Input	Input	Input	Input	Input	
P0.0		CAN. NO_TXD	CCU80. OUT21	LEDT50. COL2					U1C1. DX0D	ETH0. CLK_RMIB	ERU0. 0B0					ETH0. CLKRXB	
P0.1	USB. DRIVEVBUS	U1C1. DOUT0	CCU80. OUT11	LEDT50. COL3						ETH0. CRS_DVB	ERU0. 0A0					ETH0. RXDVB	
P0.2		U1C1. SELO1	CCU80. OUT10		U1C0. DOUT3	EBU. AD0	U1C0. HWIN3	EBU. D0	ETH0. RXD0B		ERU0. 3B3						
P0.3			CCU80. OUT20		U1C0. DOUT2	EBU. AD1	U1C0. HWIN2	EBU. D1	ETH0. RXD1B			ERU1. 3B0					
P0.4	ETH0. TX_EN		CCU80. OUT10		U1C0. DOUT1	EBU. AD2	U1C0. HWIN1	EBU. D2		U1C0. DX0A	ERU0. 2B3						
P0.5	ETH0. TXD0	U1C0. DOUT0	CCU80. OUT00		U1C0. DOUT0	EBU. AD3	U1C0. HWIN0	EBU. D3		U1C0. DX0B		ERU1. 3A0					
P0.6	ETH0. TXD1	U1C0. SELO0	CCU80. OUT30			EBU. ADV				U1C0. DX2A	ERU0. 3B2			CCU80. IN2B			
P0.7	WWDT. SERVICE_OUT	U0C0. SELO0				EBU. AD6	DB. TDI	EBU. D6	U0C0. DX2B	DSD. DIN1A	ERU0. 2B1			CCU80. IN0A	CCL80. IN1A	CCL80. IN2A	CCU80. IN3A
P0.8	SCU. EXTCLK	U0C0. SCLKOUT				EBU. AD7	DB. TRST	EBU. D7	U0C0. DX1B	DSD. DIN0A	ERU0. 2A1			CCU80. IN1B			
P0.9		U1C1. SELO0	CCU80. OUT12	LEDT50. COL0	ETH0. MOD	EBU. CST	ETH0. MDIA		U1C1. DX2A	USB. ID	ERU0. 1B0						
P0.10	ETH0. MDC	U1C1. SCLKOUT	CCU80. OUT02	LEDT50. COL1					U1C1. DX1A		ERU0. 1A0						
P0.11		U1C0. SCLKOUT	CCU80. OUT31		SDMMC. RST	EBU. BREQ			ETH0. RXERB	U1C0. DX1A	ERU0. 3A2						
P0.12		U1C1. SELO0	CCU40. OUT3			EBU. HLDA		EBU. HLDA		U1C1. DX2B	ERU0. 2B2						
P0.13		U1C1. SCLKOUT	CCU40. OUT2							U1C1. DX1B	ERU0. 2A2						
P0.14		U1C0. SELO1	CCU40. OUT1		U1C1. DOUT3		U1C1. HWIN3							CCU42. IN3C			
P0.15		U1C0. SELO2	CCU40. OUT0		U1C1. DOUT2		U1C1. HWIN2							CCU42. IN2C			
P1.0	DSD. CGPWMM	U0C0. SELO0	CCU40. OUT3	ERU1. PDOUT3					U0C0. DX2A		ERU0. 3B0			CCU40. IN3A			
P1.1	DSD. CGPWMP	U0C0. SCLKOUT	CCU40. OUT2	ERU1. PDOUT2			SDMMC. SDWC		U0C0. DX1A	POSIF0. IN2A	ERU0. 3A0			CCU40. IN2A			
P1.2			CCU40. OUT1	ERU1. PDOUT1	U0C0. DOUT3	EBU. AD14	U0C0. HWIN3	EBU. D14		POSIF0. IN1A		ERU1. 2B0		CCU40. IN1A			
P1.3		U0C0. MCLKOUT	CCU40. OUT0	ERU1. PDOUT0	U0C0. DOUT2	EBU. AD15	U0C0. HWIN2	EBU. D15		POSIF0. IN0A		ERU1. 2A0		CCU40. IN0A			
P1.4	WWDT. SERVICE_OUT	CAN. NO_TXD	CCU80. OUT33	CCU81. OUT20	U0C0. DOUT1		U0C0. HWIN1		U0C0. DX0B	CAN. INT_RXDD	ERU0. 2B0			CCU41. IN0C			

**Table 13**      **Overload Parameters**

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
Input current on any port pin during overload condition	$I_{OV}$	SR	-5	–	5	mA	
Absolute sum of all input circuit currents for one port group during overload condition <sup>1)</sup>	$I_{OVG}$	SR	–	–	20	mA	$\Sigma I_{OVx} $ , for all $I_{OVx} < 0$ mA
			–	–	20	mA	$\Sigma I_{OVx} $ , for all $I_{OVx} > 0$ mA
Absolute sum of all input circuit currents during overload condition	$I_{OVS}$	SR	–	–	80	mA	$\Sigma I_{OVG}$

1) The port groups are defined in [Table 16](#).

**Figure 11** shows the path of the input currents during overload via the ESD protection structures. The diodes against  $V_{DDP}$  and ground are a simplified representation of these ESD protection structures.



**Figure 11**      **Input Overload Current via ESD structures**

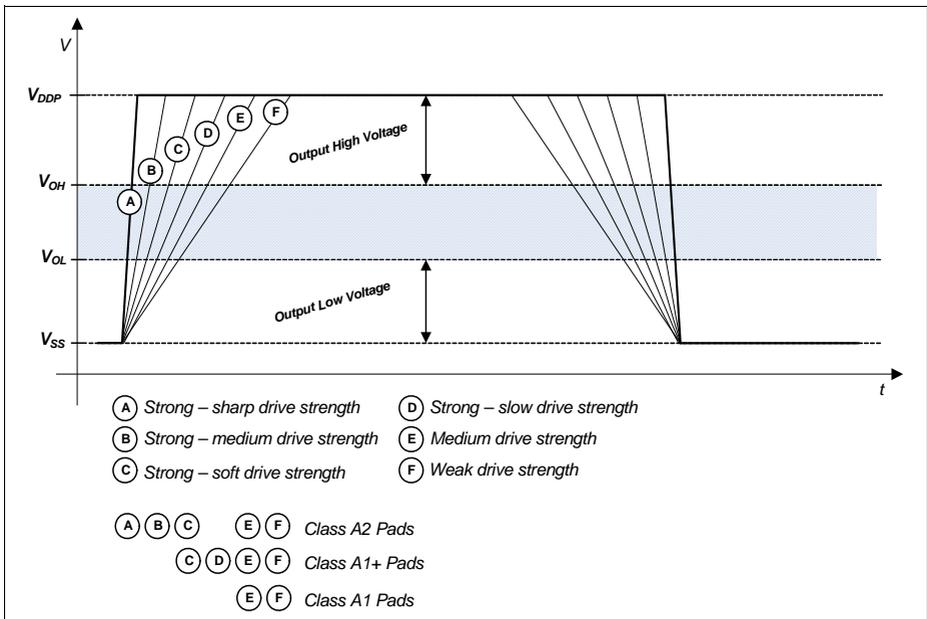
[Table 14](#) and [Table 15](#) list input voltages that can be reached under overload conditions. Note that the absolute maximum input voltages as defined in the [Absolute Maximum Ratings](#) must not be exceeded during overload.

### 3.1.4 Pad Driver and Pad Classes Summary

This section gives an overview on the different pad driver classes and their basic characteristics.

**Table 17 Pad Driver and Pad Classes Overview**

Class	Power Supply	Type	Sub-Class	Speed Grade	Load	Termination
A	3.3 V	LVTTTL I/O	<b>A1</b> (e.g. GPIO)	6 MHz	100 pF	No
			<b>A1+</b> (e.g. serial I/Os)	25 MHz	50 pF	Series termination recommended
			<b>A2</b> (e.g. ext. Bus)	80 MHz	15 pF	Series termination recommended



**Figure 12 Output Slopes with different Pad Driver Modes**

**Figure 12** is a qualitative display of the resulting output slope performance with different output driver modes. The detailed input and output characteristics are listed in [Section 3.2.1](#).

## 3.2 DC Parameters

### 3.2.1 Input/Output Pins

The digital input stage of the shared analog/digital input pins is identical to the input stage of the standard digital input/output pins.

The Pull-up on the PORST pin is identical to the Pull-up on the standard digital input/output pins.

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

**Table 19 Standard Pad Parameters**

Parameter	Symbol	Values		Unit	Note / Test Condition
		Min.	Max.		
Pin capacitance (digital inputs/outputs)	$C_{IO}$ CC	–	10	pF	
Pull-down current	$ I_{PDL} $ CC	150	–	$\mu\text{A}$	<sup>1)</sup> $V_{IN} \geq 0.6 \times V_{DDP}$
		–	10	$\mu\text{A}$	<sup>2)</sup> $V_{IN} \leq 0.36 \times V_{DDP}$
Pull-Up current	$ I_{PUH} $ CC	–	10	$\mu\text{A}$	<sup>2)</sup> $V_{IN} \geq 0.6 \times V_{DDP}$
		100	–	$\mu\text{A}$	<sup>1)</sup> $V_{IN} \leq 0.36 \times V_{DDP}$
Input Hysteresis for pads of all A classes <sup>3)</sup>	$H Y S A$ CC	$0.1 \times V_{DDP}$	–	V	
PORST spike filter always blocked pulse duration	$t_{SF1}$ CC	–	10	ns	
PORST spike filter pass-through pulse duration	$t_{SF2}$ CC	100	–	ns	
PORST pull-down current	$ I_{PPD} $ CC	13	–	mA	$V_{IN} = 1.0 \text{ V}$

1) Current required to override the pull device with the opposite logic level (“force current”).

With active pull device, at load currents between force and keep current the input state is undefined.

2) Load current at which the pull device still maintains the valid logic level (“keep current”).

With active pull device, at load currents between force and keep current the input state is undefined.

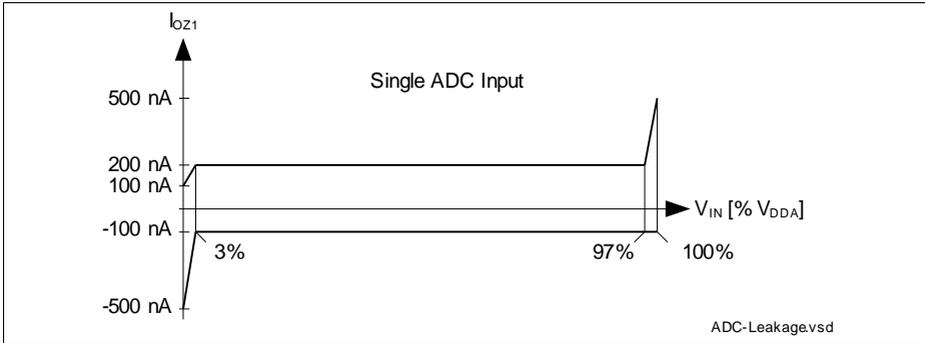
3) Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It can not be guaranteed that it suppresses switching due to external system noise.

### 3.2.2 Analog to Digital Converters (VADC)

Note: These parameters are not subject to production test, but verified by design and/or characterization.

**Table 23 VADC Parameters (Operating Conditions apply)**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Analog reference voltage <sup>5)</sup>	$V_{AREF}$ SR	$V_{AGND} + 1$	–	$V_{DDA} + 0.05^{1)}$	V	
Analog reference ground <sup>5)</sup>	$V_{AGND}$ SR	$V_{SSM} - 0.05$	–	$V_{AREF} - 1$	V	
Analog reference voltage range <sup>2)5)</sup>	$V_{AREF} - V_{AGND}$ SR	1	–	$V_{DDA} + 0.1$	V	
Analog input voltage	$V_{AIN}$ SR	$V_{AGND}$	–	$V_{DDA}$	V	
Input leakage at analog inputs <sup>3)</sup>	$I_{OZ1}$ CC	-100	–	200	nA	$0.03 \times V_{DDA} < V_{AIN} < 0.97 \times V_{DDA}$
		-500	–	100	nA	$0 V \leq V_{AIN} \leq 0.03 \times V_{DDA}$
		-100	–	500	nA	$0.97 \times V_{DDA} \leq V_{AIN} \leq V_{DDA}$
Input leakage current at VAREF	$I_{OZ2}$ CC	-1	–	1	$\mu A$	$0 V \leq V_{AREF} \leq V_{DDA}$
Input leakage current at VAGND	$I_{OZ3}$ CC	-1	–	1	$\mu A$	$0 V \leq V_{AGND} \leq V_{DDA}$
Internal ADC clock	$f_{ADCI}$ CC	2	–	30	MHz	$V_{DDA} = 3.3 V$
Switched capacitance at the analog voltage inputs <sup>4)</sup>	$C_{AINSW}$ CC	–	7	20	pF	
Total capacitance of an analog input	$C_{AINTOT}$ CC	–	25	30	pF	
Switched capacitance at the positive reference voltage input <sup>5)6)</sup>	$C_{AREFSW}$ CC	–	15	30	pF	
Total capacitance of the voltage reference inputs <sup>5)</sup>	$C_{AREFTOT}$ CC	–	20	40	pF	



**Figure 16 VADC Analog Input Leakage Current**

**Conversion Time**

**Table 24 Conversion Time (Operating Conditions apply)**

Parameter	Symbol	Values	Unit	Note
Conversion time	$t_C$ CC	$2 \times T_{ADC} + (2 + N + STC + PC + DM) \times T_{ADCI}$	$\mu\text{s}$	N = 8, 10, 12 for N-bit conversion $T_{ADC} = 1 / f_{PERIPH}$ $T_{ADCI} = 1 / f_{ADCI}$

- STC defines additional clock cycles to extend the sample time
- PC adds two cycles if post-calibration is enabled
- DM adds one cycle for an extended conversion time of the MSB

**Conversion Time Examples**

System assumptions:

$f_{ADC} = 120 \text{ MHz}$  i.e.  $t_{ADC} = 8.33 \text{ ns}$ ,  $DIVA = 3$ ,  $f_{ADCI} = 30 \text{ MHz}$  i.e.  $t_{ADCI} = 33.3 \text{ ns}$

According to the given formulas the following minimum conversion times can be achieved (STC = 0, DM = 0):

12-bit post-calibrated conversion (PC = 2):

$$t_{CN12C} = (2 + 12 + 2) \times t_{ADCI} + 2 \times t_{ADC} = 16 \times 33.3 \text{ ns} + 2 \times 8.33 \text{ ns} = 550 \text{ ns}$$

12-bit uncalibrated conversion:

$$t_{CN12} = (2 + 12) \times t_{ADCI} + 2 \times t_{ADC} = 14 \times 33.3 \text{ ns} + 2 \times 8.33 \text{ ns} = 483 \text{ ns}$$

10-bit uncalibrated conversion:

$$t_{CN10} = (2 + 10) \times t_{ADCI} + 2 \times t_{ADC} = 12 \times 33.3 \text{ ns} + 2 \times 8.33 \text{ ns} = 417 \text{ ns}$$

8-bit uncalibrated:

$$t_{CN8} = (2 + 8) \times t_{ADCI} + 2 \times t_{ADC} = 10 \times 33.3 \text{ ns} + 2 \times 8.33 \text{ ns} = 350 \text{ ns}$$

### 3.2.4 Out-of-Range Comparator (ORC)

The Out-of-Range Comparator (ORC) triggers on analog input voltages ( $V_{AIN}$ ) above the analog reference<sup>1)</sup> ( $V_{AREF}$ ) on selected input pins (GxORCy) and generates a service request trigger (GxORCOUTy).

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

The parameters in **Table 26** apply for the maximum reference voltage  $V_{AREF} = V_{DDA} + 50 \text{ mV}$ .

**Table 26 ORC Parameters** (Operating Conditions apply)

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
DC Switching Level	$V_{ODC}$	CC	100	125	200	mV	$V_{AIN} \geq V_{AREF} + V_{ODC}$
Hysteresis	$V_{OHYS}$	CC	50	–	$V_{ODC}$	mV	
Detection Delay of a persistent Overvoltage	$t_{ODD}$	CC	55	–	450	ns	$V_{AIN} \geq V_{AREF} + 200 \text{ mV}$
			45	–	105	ns	$V_{AIN} \geq V_{AREF} + 400 \text{ mV}$
Always detected Overvoltage Pulse	$t_{OPDD}$	CC	440	–	–	ns	$V_{AIN} \geq V_{AREF} + 200 \text{ mV}$
			90	–	–	ns	$V_{AIN} \geq V_{AREF} + 400 \text{ mV}$
Never detected Overvoltage Pulse	$t_{OPDN}$	CC	–	–	49	ns	$V_{AIN} \geq V_{AREF} + 200 \text{ mV}$
			–	–	30	ns	$V_{AIN} \geq V_{AREF} + 400 \text{ mV}$
Release Delay	$t_{ORD}$	CC	65	–	105	ns	$V_{AIN} \leq V_{AREF}$
Enable Delay	$t_{OED}$	CC	–	100	200	ns	

1) Always the standard VADC reference, alternate references do not apply to the ORC.

### 3.2.6 USB OTG Interface DC Characteristics

The Universal Serial Bus (USB) Interface is compliant to the USB Rev. 2.0 Specification and the OTG Specification Rev. 1.3. High-Speed Mode is not supported.

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

**Table 28 USB OTG VBUS and ID Parameters (Operating Conditions apply)**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
VBUS input voltage range	$V_{IN}$ CC	0.0	–	5.25	V	
A-device VBUS valid threshold	$V_{B1}$ CC	4.4	–	–	V	
A-device session valid threshold	$V_{B2}$ CC	0.8	–	2.0	V	
B-device session valid threshold	$V_{B3}$ CC	0.8	–	4.0	V	
B-device session end threshold	$V_{B4}$ CC	0.2	–	0.8	V	
VBUS input resistance to ground	$R_{VBUS\_IN}$ CC	40	–	100	kOhm	
B-device VBUS pull-up resistor	$R_{VBUS\_PU}$ CC	281	–	–	Ohm	Pull-up voltage = 3.0 V
B-device VBUS pull-down resistor	$R_{VBUS\_PD}$ CC	656	–	–	Ohm	
USB.ID pull-up resistor	$R_{UID\_PU}$ CC	14	–	25	kOhm	
VBUS input current	$I_{VBUS\_IN}$ CC	–	–	150	$\mu$ A	$0\text{ V} \leq V_{IN} \leq 5.25\text{ V}$ : $T_{AVG} = 1\text{ ms}$

### 3.3.4 Phase Locked Loop (PLL) Characteristics

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

#### Main and USB PLL

**Table 36 PLL Parameters**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Accumulated Jitter	$D_P$ CC	–	–	±5	ns	accumulated over 300 cycles $f_{SYS} = 120$ MHz
Duty Cycle <sup>1)</sup>	$D_{DC}$ CC	46	50	54	%	Low pulse to total period, assuming an ideal input clock source
PLL base frequency	$f_{PLLBASE}$ CC	30	–	140	MHz	
VCO input frequency	$f_{REF}$ CC	4	–	16	MHz	
VCO frequency range	$f_{VCO}$ CC	260	–	520	MHz	
PLL lock-in time	$t_L$ CC	–	–	400	μs	

1) 50% for even K2 divider values, 50±(10/K2) for odd K2 divider values.

### 3.3.8 Embedded Trace Macro Cell (ETM) Timing

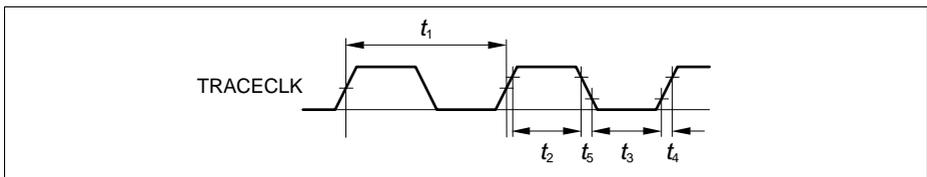
The data timing refers to the active clock edge. The XMC4500 ETM uses the half-rate clocking mode. In this mode both, the rising and falling clock edges are active clock edges.

*Note: These parameters are not subject to production test, but verified by design and/or characterization.*

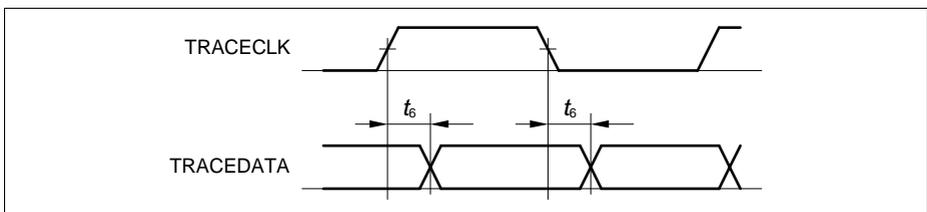
*Note: Operating conditions apply, with  $C_L \leq 15$  pF.*

**Table 41 ETM Interface Timing Parameters**

Parameter	Symbol	CC	Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
TRACECLK period	$t_1$	CC	16.7	–	–	ns	–
TRACECLK high time	$t_2$	CC	2	–	–	ns	–
TRACECLK low time	$t_3$	CC	2	–	–	ns	–
TRACECLK and TRACEDATA rise time	$t_4$	CC	–	–	3	ns	–
TRACECLK and TRACEDATA fall time	$t_5$	CC	–	–	3	ns	–
TRACEDATA output valid time	$t_6$	CC	-2	–	3	ns	–



**Figure 30 ETM Clock Timing**



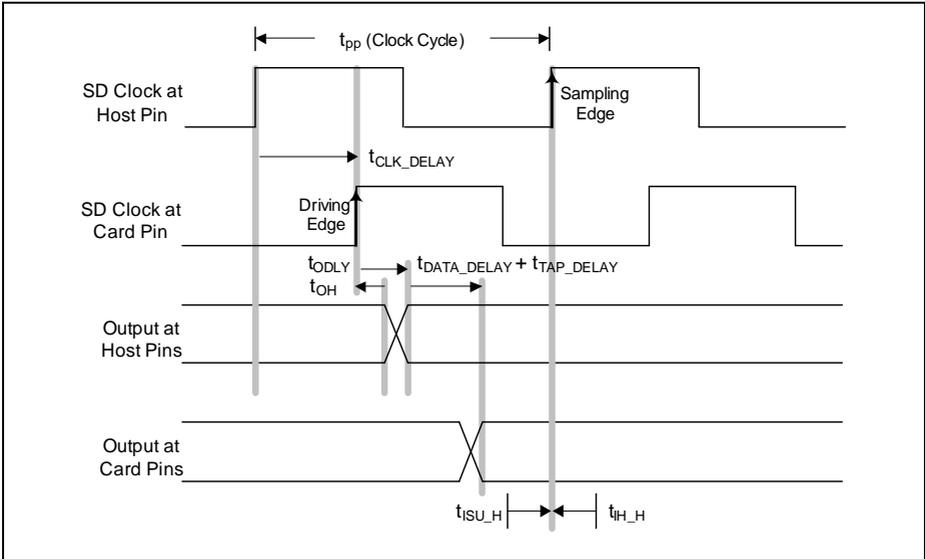
**Figure 31 ETM Data Timing**

**Table 44 USIC SSC Slave Mode Timing**

Parameter	Symbol		Values			Unit	Note / Test Condition
			Min.	Typ.	Max.		
DX1 slave clock period	$t_{CLK}$	SR	66.6	–	–	ns	
Select input DX2 setup to first clock input DX1 transmit edge <sup>1)</sup>	$t_{10}$	SR	3	–	–	ns	
Select input DX2 hold after last clock input DX1 receive edge <sup>1)</sup>	$t_{11}$	SR	4	–	–	ns	
Receive data input DX0/DX[5:3] setup time to shift clock receive edge <sup>1)</sup>	$t_{12}$	SR	6	–	–	ns	
Data input DX0/DX[5:3] hold time from clock input DX1 receive edge <sup>1)</sup>	$t_{13}$	SR	4	–	–	ns	
Data output DOUT[3:0] valid time	$t_{14}$	CC	0	–	24	ns	

1) This input timing is valid for asynchronous input signal handling of slave select input, shift clock input, and receive data input (bits DXnCR.DSEN = 0).

**High-Speed Input Path (Read)**



**Figure 40 High-Speed Input Path**

**High-Speed Read Meeting Setup (Maximum Delay)**

The following equations show how to calculate the allowed combined propagation delay range of the SD\_CLK and SD\_DAT/CMD signals on the PCB.

(11)

$$t_{CLK\_DELAY} + t_{DATA\_DELAY} + t_{TAP\_DELAY} + t_{ODLY} + t_{ISU\_H} < t_{pp}$$

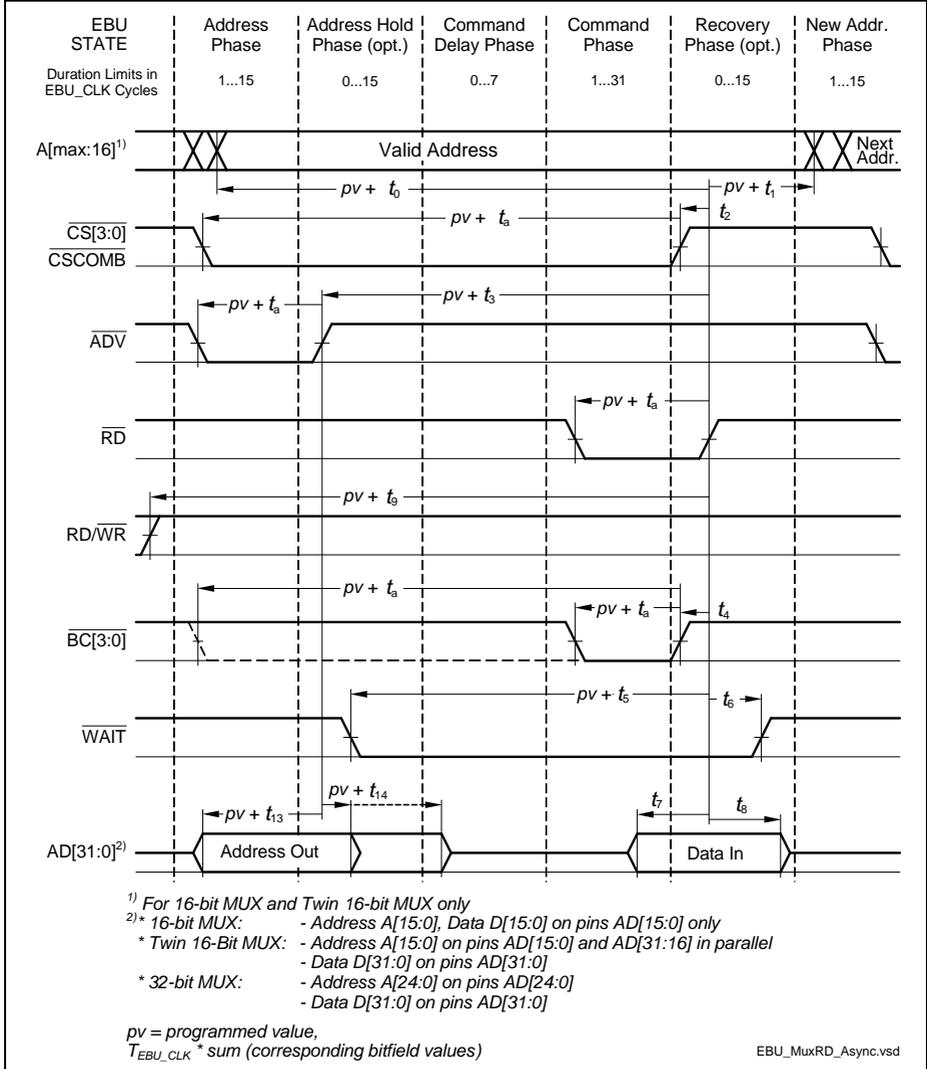
$$t_{CLK\_DELAY} + t_{DATA\_DELAY} < t_{pp} - t_{ODLY} - t_{ISU\_H} - t_{TAP\_DELAY}$$

$$t_{CLK\_DELAY} + t_{DATA\_DELAY} < 20 - 14 - 2 - t_{TAP\_DELAY}$$

$$t_{CLK\_DELAY} + t_{DATA\_DELAY} < 4 - t_{TAP\_DELAY}$$

The data + clock delay can be up to 4 ns for a 20 ns clock cycle.

Multiplexed Read Timing



**Figure 41 Multiplexed Read Access**